

Sonic Fast Recovery Diode

V_{RRM}	=	1200 V
I _{FAV}	=	10 A
t _{rr}	=	75 ns

preliminary

High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

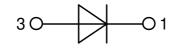
Part number

DHG10I1200PM



Backside: isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Pree wheeling didde
 Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littlefuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littlefuse.com/disclaimer-electronics.

IXYS reserves the right to change limits, conditions and dimensions.



preliminary

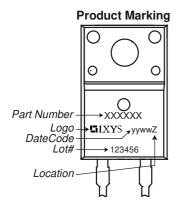
Fast Diode					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
V _{RRM}	max. repetitive reverse blocking vo	bltage	$T_{v_J} = 25^{\circ}C$			1200	V	
I _R	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			15	μA	
		V _R = 1200 V	$T_{v_J} = 125^{\circ}C$			1.2	mA	
VF	forward voltage drop	I _F = 10 A	$T_{vJ} = 25^{\circ}C$			2.22	V	
		I _F = 20 A				2.92	V	
		$I_{F} = 10 \text{ A}$	T _{vJ} = 125°C			2.13	V	
		I _F = 20 A				3.06	V	
	average forward current	$T_c = 30^{\circ}C$	T _{vJ} = 150°C			10	Α	
		rectangular d = 0.5						
V _{F0}	threshold voltage		T _{vJ} = 150°C			1.09	V	
r _F	slope resistance } for power lo	ss calculation only				94	mΩ	
\mathbf{R}_{thJC}	thermal resistance junction to case	2				4	K/W	
R thCH	thermal resistance case to heatsin	k			0.5		K/W	
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			30	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0 V$	$T_{vJ} = 45^{\circ}C$			65	Α	
C	junction capacitance	$V_{R} = 600 V f = 1 MHz$	$T_{vJ} = 25^{\circ}C$		4		pF	
I _{RM}	max. reverse recovery current		$T_{vJ} = 25 °C$		8		Α	
		$I_{\rm F} = 10 \text{ A}; V_{\rm R} = 800 \text{ V}$	T _{vj} = °C		tbd		Α	
t _{rr}	reverse recovery time	_F = 10 A; V _R = 800 V -di _F /dt = 350 A/μs	$T_{VJ} = 25 ^{\circ}C$		75		ns	
	J		T _{vj} = °C		tbd		ns	

20200213b



preliminary

Package	Package TO-220FP					Ratings		
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					35	Α
T _{vj}	virtual junction temperature				-55		150	°C
T _{op}	operation temperature				-55		125	°C
T _{stg}	storage temperature				-55		150	°C
Weight						2		g
M _D	mounting torque				0.4		0.6	Nm
F _c	mounting force with clip				20		60	Ν
d _{Spp/App}	creepage distance on surface	ctriking distance through air	terminal to terminal	3.2	2.7			mm
d _{Spb/Apb}	creepage uistance on surface	Sunking distance unough an	terminal to backside	2.5	2.5			mm
V	isolation voltage	t = 1 second			2500			V
		t = 1 minute	50/60 Hz, RMS; liso∟ ≤ 1 mA		2100			V



Part description

D = Diode H = Sonic Fast Recovery Diode

G = extreme fast

10 = Current Rating [A]

- I = Single Diode
- 1200 = Reverse Voltage [V] PM = TO-220ACFP (2)

[Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	DHG10I1200PM	DHG10I1200PM	Tube	50	503672

Similar Part	Package	Voltage class
DHG10I1200PA	TO-220AC (2)	1200

Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150^{\circ}C$
)[R	Fast Diode		
V _{0 max}	threshold voltage	1.09		V
$\mathbf{R}_{0 \max}$	slope resistance *	91		mΩ

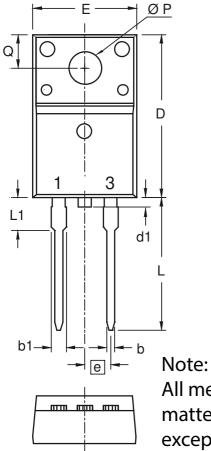
IXYS reserves the right to change limits, conditions and dimensions.

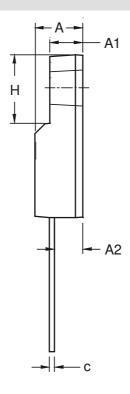
20200213b



preliminary

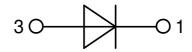
Outlines TO-220FP





All metal surface are matte pure tin plated except trimmed area.

Dim.	Millim	neters	Incl	hes
Din.	min	max	min	max
Α	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
b1	1.27	1.47	0.050	0.058
С	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
d1	0	1.10	0	0.043
Е	9.96	10.36	0.392	0.408
е	2.54	BSC	0.100 BSC	
Н	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
ØΡ	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134



20200213b

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Diodes - General Purpose, Power, Switching category:

Click to view products by IXYS manufacturer:

Other Similar products are found below :

RD0306T-H BAQ33-GS18 BAV17-TR BAV19-TR 1N3611 NTE156A NTE525 NTE571 NTE574 NTE5804 NTE5806 NTE6244 1SS181-TP 1SS193,LF 1SS400CST2RA SDAA13 SHN2D02FUTW1T1G LS4151GS08 1N4449 1N456A 1N4934-E3/73 1N914B 1N914BTR RFUH20TB3S BAS 28 E6327 BAV199-TP BAW56DWQ-7-F BAW75-TAP MM230L-CAA IDW40E65D1 LL4151-GS18 053684A SMMSD4148T3G 707803H SP000010217 ACDSW4448-HF CDSZC01100-HF BAV199E6433HTMA1 BAV70M3T5G SMBT2001T1G NTE5801 NTE5800 NTE5808 NTE6240 NTE6248 DLM10C-AT1 BAS28-7 BAW56HDW-13 BAS28 TR VS-HFA04SD60STR-M3